

Michael Lw Thewalt

List of Publications by Year in descending order

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71102

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254
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254
docs citations

254
times ranked

4632
citing authors

#	ARTICLE	IF	CITATIONS
1	Silicon-Integrated Telecommunications Photon-Spin Interface. PRX Quantum, 2020, 1, .	9.2	56
2	Shallow donor complexes formed by pairing of double-donor magnesium with group-III acceptors in silicon. Physical Review B, 2019, 99, .	3.2	9
3	Characterization of the $\text{Si} : \text{Se}^+$ Spin-Photon Interface. Physical Review Applied, 2019, 11, .	3.8	16
4	Linear Hyperfine Tuning of Donor Spins in Silicon Using Hydrostatic Strain. Physical Review Letters, 2018, 120, 167701.	7.8	34
5	Short lifetime components in the relaxation of boron acceptors in silicon. Physical Review B, 2018, 97, .	3.2	2
6	NMR study of optically hyperpolarized phosphorus donor nuclei in silicon. Physical Review B, 2018, 98, .	3.2	1
7	Highly enriched ^{28}Si reveals remarkable optical linewidths and fine structure for well-known damage centers. Physical Review B, 2018, 98, .	3.2	33
8	Mg-pair isoelectronic bound exciton identified by its isotopic fingerprint in ^{28}Si . Physical Review B, 2018, 98, .	3.2	6
9	Zero-field optical magnetic resonance study of phosphorus donors in ^{28}Si . Physical Review B, 2018, 97, .	3.2	9
10	Further investigations of the deep double donor magnesium in silicon. Physical Review B, 2018, 98, .	3.2	11
11	Competition between homogeneous and inhomogeneous broadening of orbital transitions in Si:Bi. Physical Review B, 2017, 96, .	3.2	7
12	Even-parity excited states of the acceptor boron in silicon revisited. Physical Review B, 2016, 93, .	3.2	8
13	Nuclear spin decoherence of neutral ^{31}P donors in silicon: Effect of environmental ^{29}Si	3.2	5
14	Reaching the quantum limit of sensitivity in electron spin resonance. Nature Nanotechnology, 2016, 11, 253-257.	31.5	141
15	Optical pumping and readout of bismuth hyperfine states in silicon for atomic clock applications. Scientific Reports, 2015, 5, 10493.	3.3	16
16	Hybrid optical-electrical detection of donor electron spins with bound excitons in silicon. Nature Materials, 2015, 14, 490-494.	27.5	29
17	Inductive Measurement of Optically Hyperpolarized Phosphorous Donor Nuclei in an Isotopically Enriched Silicon-28 Crystal. Physical Review Letters, 2014, 113, 267604.	7.8	15
18	Fast, low-power manipulation of spin ensembles in superconducting microresonators. Applied Physics Letters, 2014, 104, .	3.3	63

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19	Host isotope mass effects on the hyperfine interaction of group-V donors in silicon. Physical Review B, 2014, 90, .	3.2	8
20	Room-Temperature Quantum Bit Storage Exceeding 39 Minutes Using Ionized Donors in Silicon-28. Science, 2013, 342, 830-833.	12.6	341
21	InAs/InAsSb strain balanced superlattices for optical detectors: Material properties and energy band simulations. Journal of Applied Physics, 2012, 111, 034507.	2.5	54
22	Quantum Information Storage for over 180 s Using Donor Spins in a ^{28}Si Semiconductor Vacuum. Science, 2012, 336, 1280-1283.	12.6	269
23	Photoluminescence of deep defects involving transition metals in Si: New insights from highly enriched ^{28}Si . Journal of Applied Physics, 2011, 110, .	2.5	41
24	Optically-detected NMR of optically-hyperpolarized ^{31}P neutral donors in ^{28}Si . Journal of Applied Physics, 2011, 109, .	2.5	36
25	Correlation of residual impurity concentration and acceptor electron paramagnetic resonance linewidth in isotopically engineered Si. Applied Physics Letters, 2011, 99, 032101.	3.3	4
26	Nuclear Polarization of Phosphorus Donors in ^{28}Si by Selective Optical Pumping. AIP Conference Proceedings, 2010, , .	0.4	2
27	High Resolution Photoluminescence of Copper, Silver, Gold and Lithium-related Isoelectronic Bound Excitons in Highly Enriched ^{28}Si . AIP Conference Proceedings, 2010, , .	0.4	4
28	Electrical and optical characterization of n-InAsSb/n-GaSb heterojunctions. Journal of Applied Physics, 2010, 107, 014512.	2.5	8
29	Hyperfine Structure and Nuclear Hyperpolarization Observed in the Bound Exciton Luminescence of Bi Donors in Natural Si. Physical Review Letters, 2010, 104, 137402.	7.8	36
30	Electron paramagnetic resonance of boron acceptors in isotopically purified silicon. Physical Review B, 2010, 81, .	3.2	24
31	Isotopic fingerprints of Pt-containing luminescence centers in highly enriched ^{28}Si . Physical Review B, 2010, 81, .	3.2	10
32	Isotope effect on electron paramagnetic resonance of boron acceptors in silicon. Physical Review B, 2010, 82, .	3.2	23
33	Quantum Hall charge sensor for single-donor nuclear spin detection in silicon. New Journal of Physics, 2010, 12, 093028.	2.9	8
34	InAsSb and InPSb materials for mid infrared photodetectors. , 2010, , .		1
35	High-resolution absorption spectroscopy of the deep impurities S and Se in ^{28}Si . Physical Review B, 2009, 80, .	3.2	24
36	Single-frequency laser spectroscopy of the boron bound exciton in ^{28}Si . Physical Review B, 2009, 80, .	3.2	2

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37	Strain balanced InAs/InAsSb superlattice structures with optical emission to 10 ⁻⁴ m. Applied Physics Letters, 2009, 95, .	3.3	48
38	Homogeneous linewidth of the P31 bound exciton transition in silicon. Applied Physics Letters, 2009, 95, .	3.3	13
39	Simultaneous Subsecond Hyperpolarization of the Nuclear and Electron Spins of Phosphorus in Silicon by Optical Pumping of Exciton Transitions. Physical Review Letters, 2009, 102, 257401.	7.8	49
40	Shallow impurity absorption spectroscopy in isotopically enriched silicon. Physical Review B, 2009, 79, .	3.2	40
41	Reduction of the Linewidths of Deep Luminescence Centers inSi28Reveals Fingerprints of the Isotope Constituents. Physical Review Letters, 2008, 100, 177402.	7.8	41
42	High-resolution photoluminescence measurement of the isotopic-mass dependence of the lattice parameter of silicon. Physical Review B, 2008, 77, .	3.2	3
43	Direct observation of the donor nuclear spin in a near-gap bound exciton transition: P31 in highly enriched S28i. Journal of Applied Physics, 2007, 101, 081724.	2.5	34
44	Dicarbon defects in as-grown and annealed carbon-doped InAs. Journal of Applied Physics, 2007, 102, 083528.	2.5	6
45	Shallow Impurity Absorption Spectroscopy in Isotopically Enriched Silicon. AIP Conference Proceedings, 2007, , .	0.4	2
46	Can highly enriched 28Si reveal new things about old defects?. Physica B: Condensed Matter, 2007, 401-402, 587-592.	2.7	40
47	High resolution photoluminescence of sulphur- and copper-related isoelectronic bound excitons in highly enriched 28Si. Physica B: Condensed Matter, 2007, 401-402, 593-596.	2.7	14
48	Impurity absorption spectroscopy of the deep double donor sulfur in isotopically enriched silicon. Physica B: Condensed Matter, 2007, 401-402, 600-603.	2.7	11
49	Optical Detection and Ionization of Donors in Specific Electronic and Nuclear Spin States. Physical Review Letters, 2006, 97, 227401.	7.8	63
50	Optical and electrical characterization of OMVPE-grown AlGaAsSb epitaxial layers on InP substrates. Journal of Crystal Growth, 2006, 287, 532-535.	1.5	0
51	Microstructure of ordered nanodomains induced by Bi surfactant in OMVPE-grown GaAsSb. Journal of Crystal Growth, 2006, 287, 541-544.	1.5	3
52	Isotopic mass dependence of the lattice parameter in silicon determined by measurement of strain-induced splitting of impurity bound exciton transitions. Physica B: Condensed Matter, 2006, 376-377, 54-56.	2.7	5
53	Effects of sulfur isotopic composition on the band gap ofPbS. Physical Review B, 2006, 73, .	3.2	28
54	Raman scattering in carbon-doped InAs. Applied Physics Letters, 2006, 88, 041908.	3.3	11

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55	Local vibrational mode study of carbon-doped InAs. <i>Physical Review B</i> , 2006, 74, .	3.2	12
56	Spectroscopy of excitons and shallow impurities in isotopically enriched silicon—electronic properties beyond the virtual crystal approximation. <i>Solid State Communications</i> , 2005, 133, 715-725.	1.9	17
57	Isotope effects on the optical spectra of semiconductors. <i>Reviews of Modern Physics</i> , 2005, 77, 1173-1224.	45.6	380
58	Progress in Semiconductor Spectroscopy Using Isotopically Enriched Si. <i>AIP Conference Proceedings</i> , 2005, , .	0.4	3
59	High-Purity, Isotopically Enriched Bulk Silicon. <i>Journal of the Electrochemical Society</i> , 2005, 152, G448.	2.9	34
60	Temperature Dependence of the Energy Gap of Semiconductors in the Low-Temperature Limit. <i>Physical Review Letters</i> , 2004, 92, 196403.	7.8	75
61	Effect of Bi surfactant on atomic ordering of GaAsSb. <i>Applied Physics Letters</i> , 2004, 85, 5589-5591.	3.3	10
62	Sulfur isotope effects on the excitonic spectra of CdS. <i>Physical Review B</i> , 2004, 69, .	3.2	10
63	Ultrathin type-II GaSb/GaAs quantum wells grown by OMVPE. <i>Journal of Crystal Growth</i> , 2004, 269, 187-194.	1.5	6
64	Effect of the isotopic mass of gallium on the indirect gap of GaP. <i>Solid State Communications</i> , 2003, 126, 119-123.	1.9	11
65	Photoluminescence studies of isotopically enriched silicon. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 235, 63-74.	1.5	8
66	Electrical and optical properties of carbon-doped GaSb. <i>Physical Review B</i> , 2003, 67, .	3.2	25
67	Acceptor identification using magnetophotoluminescence of bound exciton states in InSb. <i>Physical Review B</i> , 2003, 67, .	3.2	1
68	Impurity Absorption Spectroscopy in Si ²⁸ : The Importance of Inhomogeneous Isotope Broadening. <i>Physical Review Letters</i> , 2003, 90, 186402.	7.8	67
69	Origin of the Residual Acceptor Ground-State Splitting in Silicon. <i>Physical Review Letters</i> , 2003, 90, 016404.	7.8	24
70	Dependence of the ionization energy of shallow donors and acceptors in silicon on the host isotopic mass. <i>Physical Review B</i> , 2003, 68, .	3.2	20
71	—Intrinsic—Acceptor Ground State Splitting in Silicon: An Isotopic Effect. <i>Physical Review Letters</i> , 2002, 89, 016401.	7.8	30
72	Magnetophotoluminescence of neutral acceptor states in InSb. <i>Applied Physics Letters</i> , 2002, 80, 2332-2334.	3.3	1

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73	Method for shallow impurity characterization in ultrapure silicon using photoluminescence. Journal of Applied Physics, 2002, 92, 5913-5916.	2.5	14
74	Photoluminescence studies of isotopically enriched silicon: isotopic effects on the indirect electronic band gap and phonon energies. Solid State Communications, 2002, 123, 87-92.	1.9	38
75	In-situ monitoring, structural, and optical properties of ultrathin GaSb/GaAs quantum wells grown by OMVPE. Journal of Electronic Materials, 2001, 30, 1412-1416.	2.2	11
76	P-type carbon doping of GaSb. Journal of Electronic Materials, 2001, 30, 1429-1432.	2.2	17
77	Photoluminescence method for detecting trace levels of iron in ultrapure silicon. Applied Physics Letters, 2001, 78, 3070-3072.	3.3	5
78	Photoluminescence of Isotopically Purified Silicon: How Sharp are Bound Exciton Transitions?. Physical Review Letters, 2001, 86, 6010-6013.	7.8	73
79	Magnetophotoluminescence of D^{\sim} singlet and triplet states in GaAs. Physical Review B, 1999, 60, 15527-15530.	3.2	3
80	Strain Effects on Bound Exciton Luminescence in Epitaxial GaAs Studied Using a Wafer Bending Technique. Physica Status Solidi (B): Basic Research, 1998, 210, 353-359.	1.5	5
81	Type II photoluminescence and conduction band offsets of GaAsSb/InGaAs and GaAsSb/InP heterostructures grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 1998, 73, 2799-2801.	3.3	147
82	Nearly ideal InP/GaAsSb/InP double heterojunction bipolar transistors with ballistically launched collector electrons. Electronics Letters, 1998, 34, 1700.	1.0	20
83	Lattice parameter variation in doped GaAs substrates determined using high resolution photoluminescence spectroscopy. Journal of Applied Physics, 1998, 84, 6305-6311.	2.5	2
84	High resolution spectroscopy of free-standing GaAs films prepared by epitaxial liftoff. Journal of Applied Physics, 1998, 84, 5772-5775.	2.5	0
85	New Photoluminescence Transition in GaAs Involving D^{\sim} States. Physical Review Letters, 1998, 80, 2461-2464.	7.8	3
86	Phosphorus Passivation of GaAs. Materials Research Society Symposia Proceedings, 1998, 510, 647.	0.1	2
87	Large photoluminescence enhancements from epitaxial GaAs passivated by postgrowth phosphidization. Applied Physics Letters, 1997, 70, 3275-3277.	3.3	18
88	Fourier-transform photoluminescence spectroscopy of excitons bound to group-III acceptors in silicon: D^{\sim} , Uniaxial stress. Physical Review B, 1997, 56, 15672-15684.	3.2	2
89	Type II Band Alignment in $\text{Si}_{1-x}\text{Ge}_x/\text{Si}(001)$ Quantum Wells: The Ubiquitous Type I Luminescence Results from Band Bending. Physical Review Letters, 1997, 79, 269-272.	7.8	114
90	Characterization of interfacial dopant layer for high-purity InP grown by MOCVD. Journal of Crystal Growth, 1997, 182, 23-29.	1.5	4

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91	Low-temperature photoluminescence of epitaxial InAs. Journal of Applied Physics, 1996, 80, 6416-6424.	2.5	60
92	Growth and photoluminescence of high quality SiGeC random alloys on silicon substrates. Journal of Applied Physics, 1996, 80, 3043-3047.	2.5	32
93	Photoluminescence of excitons bound to the radiation damage defects B41 (1.1509 eV) in silicon. Solid State Communications, 1996, 97, 137-142.	1.9	5
94	Polarization dependence of the Raman-active lattice modes of crystalline C60. Physical Review B, 1996, 53, 2199-2201.	3.2	4
95	Fourier-transform photoluminescence spectroscopy of excitons bound to group-III acceptors in silicon: Zeeman effect. Physical Review B, 1996, 54, 10543-10558.	3.2	10
96	Raman-scattering study of isotopically engineered crystalline C60. Physical Review B, 1996, 54, 920-929.	3.2	26
97	Defect-Free Band-Edge Photoluminescence in SiGeC Strained Layers Grown by Rapid Thermal Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1995, 379, 441.	0.1	1
98	¹³ C hyperfine coupling constants in MuC60. Chemical Physics Letters, 1995, 245, 90-94.	2.6	23
99	Splitting of the ground state of shallow acceptors in silicon. Solid State Communications, 1995, 93, 379-382.	1.9	8
100	The pressure dependence of Raman active libron modes in crystalline C60. Solid State Communications, 1995, 93, 575-578.	1.9	8
101	A comparison of techniques for nondestructive composition measurements in CdZnTe substrates. Journal of Electronic Materials, 1995, 24, 697-705.	2.2	57
102	Characterization of very high purity InAs grown using trimethylindium and tertiarybutylarsine. Journal of Electronic Materials, 1995, 24, 1583-1590.	2.2	10
103	Pressured-Induced Structural Metastability in Crystalline C60. Physical Review Letters, 1995, 74, 3483-3486.	7.8	24
104	Photoluminescence of excitons bound to the isoelectronic hydrogen-related defects B80 (1.1470 eV) and B191 (1.1431 eV) in silicon. Physical Review B, 1995, 51, 4882-4888.	3.2	4
105	Raman Fine Structure in Crystalline C60: The Effects of Merohedral Disorder, Isotopic Substitution, and Crystal Field. Physical Review Letters, 1995, 74, 194-197.	7.8	29
106	Effect of isotopic disorder on the Fumodes in crystalline C60. Physical Review B, 1995, 52, 16892-16900.	3.2	7
107	Defect-free band-edge photoluminescence and band gap measurement of pseudomorphic Si _{1-x} Ge _x alloy layers on Si (100). Applied Physics Letters, 1995, 67, 3915-3917.	3.3	109
108	Disorder, impurity, and isotope effects in the Raman-active libron spectrum of crystalline C60. Physical Review B, 1995, 52, R6951-R6954.	3.2	13

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109	Comment on "Nanosecond-Gated Detection of Room-Temperature Fluorescence of C ₆₀ in Solution". Physical Review Letters, 1995, 74, 4564-4564.	7.8	0
110	Wolk, Horoyski, and Thewalt Reply:. Physical Review Letters, 1995, 75, 2907-2907.	7.8	0
111	Comment on "Direct Determination of the Electron-Electron-Hole Auger Threshold Energy in Silicon". Physical Review Letters, 1995, 75, 3962-3962.	7.8	2
112	Sharp excitonic photoluminescence from epitaxial InAs. Applied Physics Letters, 1995, 66, 1101-1103.	3.3	26
113	High Temperature (77-300 K) Photo- and Electroluminescence in Si/Si _{1-x} Gex Heterostructures. Japanese Journal of Applied Physics, 1994, 33, 2329-2334.	1.5	21
114	Fine structure of a bound multiexciton complex in CdTe. Physical Review B, 1994, 50, 18030-18033.	3.2	2
115	Intrinsic Splitting of the Acceptor Ground State in Silicon. Physical Review Letters, 1994, 73, 2340-2343.	7.8	15
116	Electrical, optical properties, and surface morphology of high purity InP grown by chemical beam epitaxy. Journal of Applied Physics, 1994, 76, 5300-5308.	2.5	7
117	Photoluminescence of excitons bound to the isoelectronic hydrogen-related defects B711 (1.1377 eV) in silicon. Physical Review B, 1994, 50, 7338-7343.	3.2	17
118	Fourier-transform magnetophotoluminescence spectroscopy of donor-bound excitons in GaAs. Physical Review B, 1994, 49, 16381-16397.	3.2	38
119	Anomalous splitting of the F _{1u} (³ F _u) vibrations in single-crystal C ₆₀ below the orientational-ordering transition. Physical Review B, 1994, 49, 7052-7055.	3.2	30
120	Growth and band gap of strained $\sim 110^\circ$ Si _{1-x} Gex layers on silicon substrates by chemical vapor deposition. Applied Physics Letters, 1994, 65, 76-78.	3.3	32
121	C ₇₀ vibrational frequencies obtained from singlet oxygen photoluminescence. Chemical Physics Letters, 1994, 217, 409-412.	2.6	6
122	Visible photoluminescence from biexcitons in Si _{1-x} Gex quantum wells. Solid State Communications, 1994, 89, 429-432.	1.9	26
123	Fourier Transform Raman and Brillouin Spectroscopy Using Atomic Vapor Filters. Applied Spectroscopy, 1994, 48, 843-847.	2.2	15
124	Enhancement of high-temperature photoluminescence in strained Si _{1-x} Gex/Si heterostructures by surface passivation. Applied Physics Letters, 1994, 65, 3344-3346.	3.3	21
125	Deep photoluminescence in Si/Si _{1-x} Gex/Si quantum wells created by ion implantation and annealing. Applied Physics Letters, 1994, 64, 2291-2293.	3.3	26
126	Growth and Photoluminescence of Strained $\langle 110 \rangle$ Si/Si _x Gex/Si Quantum Wells Grown by Rapid Thermal Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1994, 342, 37.	0.1	3

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127	Photoluminescence and electroluminescence processes in Si $1\hat{a}^{\sim}$ xGe x /Si heterostructures grown by chemical vapor deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 21, 307-311.	3.5	0
128	Photoluminescence spectroscopy of localized excitons in Si $1\hat{a}^{\sim}$ xGe x . Journal of Electronic Materials, 1993, 22, 233-238.	2.2	15
129	Observation of autodissociating excited states of excitonic molecules. Physical Review B, 1993, 47, 1628-1631.	3.2	5
130	Exciton luminescence in Si $1\hat{a}^{\sim}$ xGe x /Si heterostructures grown by molecular beam epitaxy. Journal of Applied Physics, 1993, 74, 2790-2805.	2.5	58
131	Photoluminescence study of vertical transport in Si $1\hat{a}^{\sim}$ xGe x /Si heterostructures. Physical Review B, 1993, 47, 16659-16662.	3.2	7
132	Observation of luminescence from the EL2 metastable state in liquid-encapsulated Czochralski-grown GaAs under hydrostatic pressure. Physical Review B, 1993, 47, 1265-1269.	3.2	13
133	Photoluminescence mechanisms in thin Si $1\hat{a}^{\sim}$ xGe x quantum wells. Physical Review B, 1993, 47, 16655-16658.	3.2	35
134	Ultrahigh-resolution photoluminescence studies of excitons bound to boron in silicon in magnetic fields. Physical Review B, 1993, 47, 9354-9360.	3.2	7
135	Optically detected librions and phonons in crystalline C 60 . Physical Review B, 1993, 48, 11446-11449.	3.2	58
136	Cryogenic, whole wafer imaging of semi-insulating GaAs. Semiconductor Science and Technology, 1992, 7, A16-A21.	2.0	5
137	Formation of a DX center in InP under hydrostatic pressure. Physical Review Letters, 1992, 68, 3619-3622.	7.8	35
138	Highly structured singlet oxygen photoluminescence from crystalline C 60 . Physical Review Letters, 1992, 69, 2423-2426.	7.8	75
139	Band-edge exciton luminescence from Si/strained Si $1\hat{a}^{\sim}$ xGe x /Si structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 1998.	1.6	10
140	Quantum confinement effects in strained silicon-germanium alloy quantum wells. Applied Physics Letters, 1992, 60, 2135-2137.	3.3	67
141	High quantum efficiency photoluminescence from localized excitons in Si $1\hat{a}^{\sim}$ xGe x . Applied Physics Letters, 1992, 60, 3174-3176.	3.3	89
142	Ultrahigh-resolution photoluminescence studies of excitons bound to boron in silicon under uniaxial stress. Physical Review B, 1992, 45, 11736-11743.	3.2	15
143	Room-temperature 1.3 μ m electroluminescence from strained Si $1\hat{a}^{\sim}$ xGe x /Si quantum wells. Applied Physics Letters, 1992, 60, 3177-3179.	3.3	70
144	Photoluminescence from electron-hole plasmas confined in Si/Si $1\hat{a}^{\sim}$ xGe x /Si quantum wells. Applied Physics Letters, 1992, 60, 1720-1722.	3.3	63

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145	Donor identification in bulk GaAs by Fourier transform photoluminescence. Canadian Journal of Physics, 1991, 69, 427-431.	1.1	3
146	Well-Resolved Band-Edge Photoluminescence from Strained Si _{1-x} Ge _x Layers Grown by Rapid Thermal Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1991, 220, 341.	0.1	2
147	Float zone growth of high purity and high oxygen concentration silicon. Journal of Crystal Growth, 1991, 109, 162-166.	1.5	0
148	Enhancement of luminescence in GaAs by low levels of Cu. Applied Physics Letters, 1991, 58, 714-716.	3.3	11
149	Zeeman spectroscopy of an axial-double-acceptor bound exciton in GaAs grown by molecular-beam epitaxy. Physical Review B, 1991, 44, 13426-13434.	3.2	4
150	Well-resolved band-edge photoluminescence of excitons confined in strained Si _{1-x} Ge _x quantum wells. Physical Review Letters, 1991, 66, 1362-1365.	7.8	306
151	Photoluminescence studies of the EL2 defect in gallium arsenide under external perturbations. Physical Review Letters, 1991, 67, 112-115.	7.8	40
152	A low-temperature, whole-wafer-imaging system for defect and impurity mapping. Canadian Journal of Physics, 1991, 69, 333-338.	1.1	5
153	Quantitative, all-optical prediction of the carrier density in semi-insulating GaAs. Applied Physics Letters, 1990, 56, 647-649.	3.3	8
154	Photoluminescence study of nitrogen-oxygen donors in silicon. Applied Physics Letters, 1990, 56, 148-150.	3.3	21
155	Photoluminescence transitions of the deep EL2 defect in gallium arsenide. Physical Review Letters, 1990, 65, 2282-2285.	7.8	19
156	Photoluminescence from excitons bound to a triple acceptor, Ge:Cu. Physical Review B, 1990, 41, 7926-7928.	3.2	9
157	Optical properties of shallow defect-related acceptors in GaAs grown by molecular-beam epitaxy. Physical Review B, 1990, 41, 8221-8228.	3.2	14
158	Photoluminescence decay times of the defect-induced bound-exciton lines in GaAs grown by molecular-beam epitaxy. Physical Review B, 1990, 41, 2861-2864.	3.2	9
159	Photoluminescence studies of bound excitons in copper-doped GaAs. Journal of Applied Physics, 1990, 67, 4244-4248.	2.5	2
160	Photoluminescence studies of defects in annealed Czochralski silicon. Canadian Journal of Physics, 1989, 67, 268-274.	1.1	10
161	Optical properties of the sulfur-related isoelectronic bound excitons in Si. Physical Review B, 1989, 40, 9618-9625.	3.2	28
162	Evidence for asymmetric well shapes in post-growth modified GaAs/AlGaAs quantum wells. Journal of Applied Physics, 1989, 66, 5532-5535.	2.5	7

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163	Photoluminescence for characterization of commercial semi-insulating GaAs. Canadian Journal of Physics, 1989, 67, 384-388.	1.1	8
164	Double fluorescence lifetimes of metal-free phthalocyanine in a mixed-solvent Shpol'skii matrix at 4Å ² . Molecular Physics, 1989, 67, 1439-1443.	1.7	8
165	A photoluminescence study of zinc-implanted silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1989, 4, 201-204.	3.5	7
166	Modification of the shapes of GaAs/AlGaAs quantum wells using rapid thermal annealing. Superlattices and Microstructures, 1989, 5, 321-325.	3.1	30
167	Time-resolved studies of biexcitons in GaAs. Solid State Communications, 1989, 69, 1139-1142.	1.9	12
168	Time-dependent recombination spectra arising from optical ejection of trapped charges in feldspars. Journal of Luminescence, 1989, 44, 41-46.	3.1	33
169	Time-dependent recombination luminescence spectra arising from optical ejection of trapped charges in zircons. Journal of Luminescence, 1989, 44, 47-57.	3.1	12
170	Optical techniques for characterizing SI GaAs. Canadian Journal of Physics, 1989, 67, 242-250.	1.1	13
171	Transient photoluminescence studies of coupled double-quantum wells. Canadian Journal of Physics, 1989, 67, 315-320.	1.1	0
172	High Performance Photoluminescence Spectroscopy using Fourier Transform Interferometry. Materials Research Society Symposia Proceedings, 1989, 163, 221.	0.1	7
173	Electronic Structure of Two Sulphur-Related Bound Excitons in Silicon Studied by Optical Detection of Magnetic Resonance. Materials Research Society Symposia Proceedings, 1989, 163, 303.	0.1	0
174	Radiative recombination in highly excited ZnSe. Solid State Communications, 1988, 67, 187-191.	1.9	7
175	A new photoluminescence band in silicon lightly doped with copper. Solid State Communications, 1988, 68, 7-11.	1.9	36
176	A zinc-related isoelectronic bound exciton in silicon. Solid State Communications, 1988, 66, 689-694.	1.9	12
177	Thermoluminescence spectra of some mineral samples relevant to thermoluminescence dating. Journal of Luminescence, 1988, 39, 123-136.	3.1	100
178	Stereochemical controls on exciplex reactions. Excited state proton transfer. Journal of the American Chemical Society, 1988, 110, 5543-5547.	13.7	8
179	Transformation of spatially direct to spatially indirect excitons in coupled double quantum wells. Physical Review B, 1988, 38, 6287-6290.	3.2	64
180	A high average-power quasi-continuous optical parametric oscillator system. Canadian Journal of Physics, 1988, 66, 868-870.	1.1	4

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181	Detailed ground- and excited-state spectroscopy of indirect free excitons. Physical Review Letters, 1988, 61, 1882-1884.	7.8	35
182	Magnetophotoluminescence characterization of residual donors in GaAs grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1988, 64, 3205-3209.	2.5	18
183	Epitaxy's substrate discrimination in the photoluminescence characterization of epitaxial Si. Applied Physics Letters, 1988, 53, 666-668.	3.3	4
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